

ABSTRACT

ETCH OF SILICON NITRIDE SELECTIVE TO SILICON AND SILICON DIOXIDE USEFUL DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

A method for etching silicon nitride selective to silicon dioxide and silicon (polycrystalline silicon or monocrystalline silicon) comprises the use of oxygen along with an additional etchant of either CHF_3 or CH_2F_2 . Flow rates, power, and pressure settings are specified.

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